

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	18	(multiple) adj2 (gate) adj2 (insulator)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 09:20
S2	16	S1 and (@ad<="20031205")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 07:18
S3	198	(multiple) adj2 (oxide) adj2 ((insulator) or (layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 16:35
S4	182	S3 and (@ad<="20031205")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 16:36
S5	326	(photoresist) and ((ozone) adj2 (water)) and (@ad<="20031205")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 07:22
S6	136	(photoresist) same ((ozone) adj2 (water)) and (@ad<="20031205")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 07:37
S7	136	(photoresist) same ((ozon\$4) adj2 (water)) and (oxid\$5) and (@ad<="20031205")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 07:39
S8	72	(photoresist) same ((ozon\$4) adj2 (water)) same (oxid\$5) and (@ad<="20031205")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 07:39
S9	617	(multiple) adj3 (insulator)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 09:22
S10	287	(multiple) adj3 (insulator) and (silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 09:54

S13	4435	(multiple) same (gate) same ((insulator) or (oxide) or (dielectric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 10:26
S14	3558	(multiple) same (gate) same ((insulator) or (oxide) or (dielectric)) and (silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 10:29
S15	566	(multiple) adj3 (gate) same ((insulator) or (oxide) or (dielectric)) and (silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 10:32
S16	52	(multiple) adj3 (gate.TI.) same ((insulator) or (oxide) or (dielectric)) and (silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 12:13
S17	77	(multi-gate) same ((insulator) or (oxide) or (dielectric)) and (silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 11:15
S18	7	(double-gate.TI.) same ((insulator) or (oxide) or (dielectric)) and (silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 11:17
S19	269	(double-gate) same ((insulator) or (oxide) or (dielectric)) and (silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 11:17
S20	166	(multiple) adj3 (gate.TI.) and ((insulator) or (oxide) or (dielectric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 12:14
S22	0	("(5858106)(5454901)(6513538)").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 12:59
S23	2	("(5858106)").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 12:59
S24	2	("(5454901)").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 13:01

S25	2	("(6513538)").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/03 13:00
S32	3	(clean.TI.) and (photoresist) and (SPM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 07:21
S33	108266	(remov\$3) and (photoresist)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 07:23
S34	221	(remov\$3) and (photoresist) and (SPM) and (temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 07:24
S35	1	("20050158671").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/05 08:58